

SuperMOS – SOP8 100V BV_{DSS}, 120mΩ R_{DS(ON)}, N-channel MOSFET

1. Description

The ESP10N10C is N-Channel enhancement MOS Field Effect Transistor. Uses advanced trench technology and design to provide excellent R_{DS(ON)} with low gate charge. Device is suitable for use in DC-DC conversion, power switch and charging circuit. Standard Product ESP10N10C is Pb-free.

2. Features

- 100V, R_{DS(ON)}=120mΩ(TYP.) @V_{GS}=10V
R_{DS(ON)}=130mΩ(TYP.) @V_{GS}=4.5V
 - High density cell design for low R_{DS(on)}
 - Material: Halogen free
- Reliable and rugged
 - Avalanche Rated
 - Low leakage current

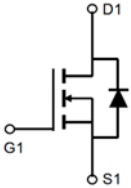
3. Applications

- PWM applications
 - Load switch
 - Power management in portable/desktop PCs
 - DC/DC conversion
- 100% UIS TESTED

4. Ordering Information

Part Number	Package	Marking	Material	Packing	Quantity per reel	Flammability Rating	Reel Size
ESP10N10C	SOP8	10N10C/lot	Halogen free	Tape & Reel	3,000 PCS	UL 94V-0	13 inches

5. Pin Configuration and Functions

Pin	Function	Outline	Circuit Diagram
4	Gate	Note b 	
1/2/3	Source		
5/6/7/8	Drain		

6. Specification

Absolute Maximum Rating & Thermal Characteristics

Ratings at 25 °C ambient temperature unless otherwise specified.

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		BV_{DSS}	100	V
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current	$T_A=25^{\circ}\text{C}$	I_D	4.5	A
	$T_A=100^{\circ}\text{C}$		3.0	
Maximum Power Dissipation		P_D	3.1	W
Pulsed Drain Current		I_{DM}	18	A
Avalanche Current, Single Pulsed ^a		I_{AS}	9	A
Avalanche Energy, Single Pulsed ^a		E_{AS}	12	mJ
Operating Junction Temperature		T_J	150	$^{\circ}\text{C}$
Lead Temperature		T_L	260	$^{\circ}\text{C}$
Storage Temperature Range		T_{stg}	-55 to 150	$^{\circ}\text{C}$

Thermal resistance ratings

Single Operation				
Parameter	Symbol	Typical	Maximum	Unit
Junction-to-Ambient Thermal Resistance	$R_{\theta JA}$		40	$^{\circ}\text{C/W}$

Note:

a: EAS condition: $T_J=25^{\circ}\text{C}$, $V_{DD}=100\text{V}$, $V_G=10\text{V}$, $L=0.3\text{mH}$, $R_g=25\Omega$

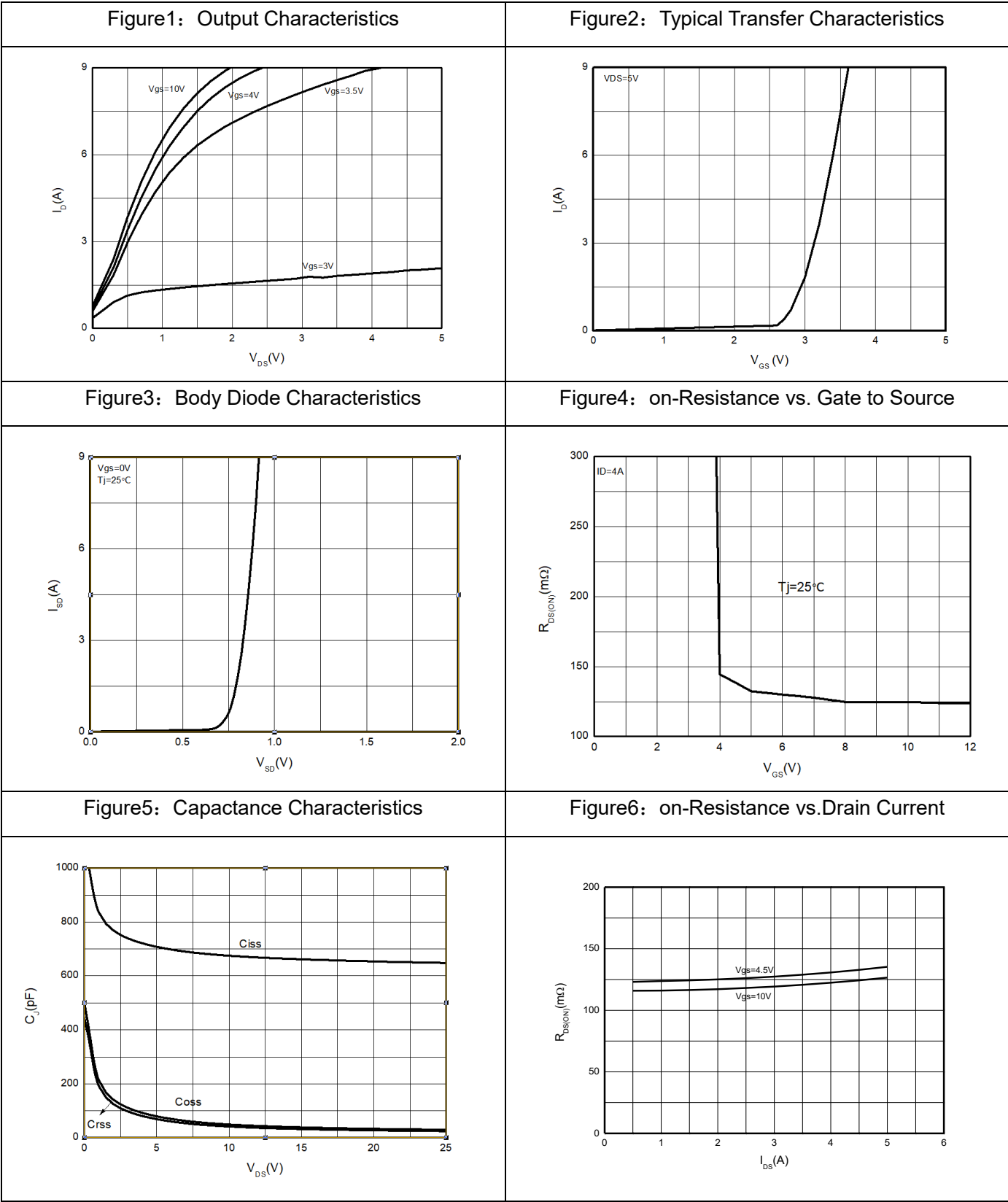
b: This diagram is only an electrical schematic, and the actual pin size is based on POD.

Electrical Characteristics

At TA = 25°C unless otherwise specified

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250uA	100			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =100V, V _{GS} =0V			1	uA
Gate-to-source Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±20V			±100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	V _{GS(TH)}	V _{GS} =V _{DS} , I _D =250uA	1.0	1.7	2.5	V
Drain-to-source On-resistance	R _{DS(on)}	V _{GS} =10V, I _D =4A		120	150	mΩ
		V _{GS} =4.5V, I _D =3A		130	180	
CHARGES, CAPACITANCES AND GATE RESISTANCE						
Input Capacitance	C _{ISS}	V _{GS} =0V, f=1MHz, V _{DS} =25V		650		pF
Output Capacitance	C _{OSS}			30		
Reverse Transfer Capacitance	C _{RSS}			25		
BODY DIODE CHARACTERISTICS						
Forward Voltage	V _{SD}	V _{GS} =0V, I _S =4A			1.5	V

7. Typical Characteristics

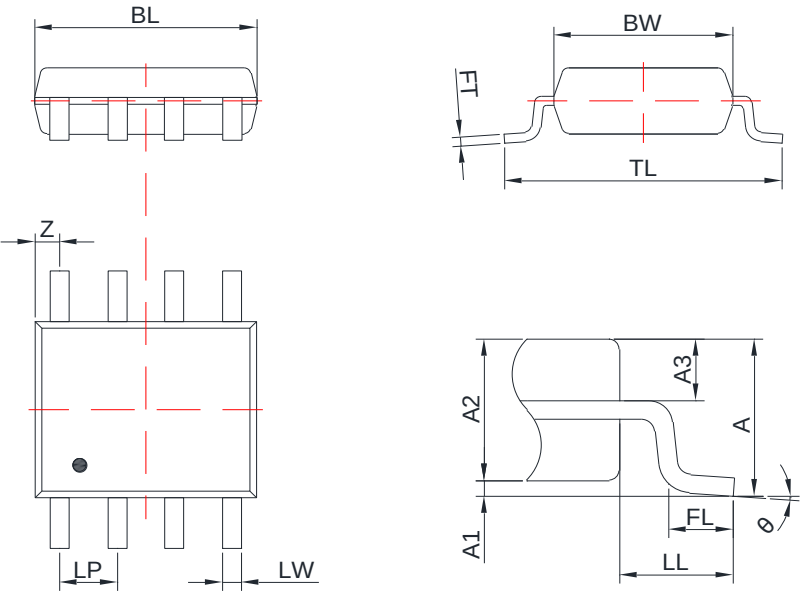


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Rev-1.5

8. Dimension (SOP8)

POD A(Y)



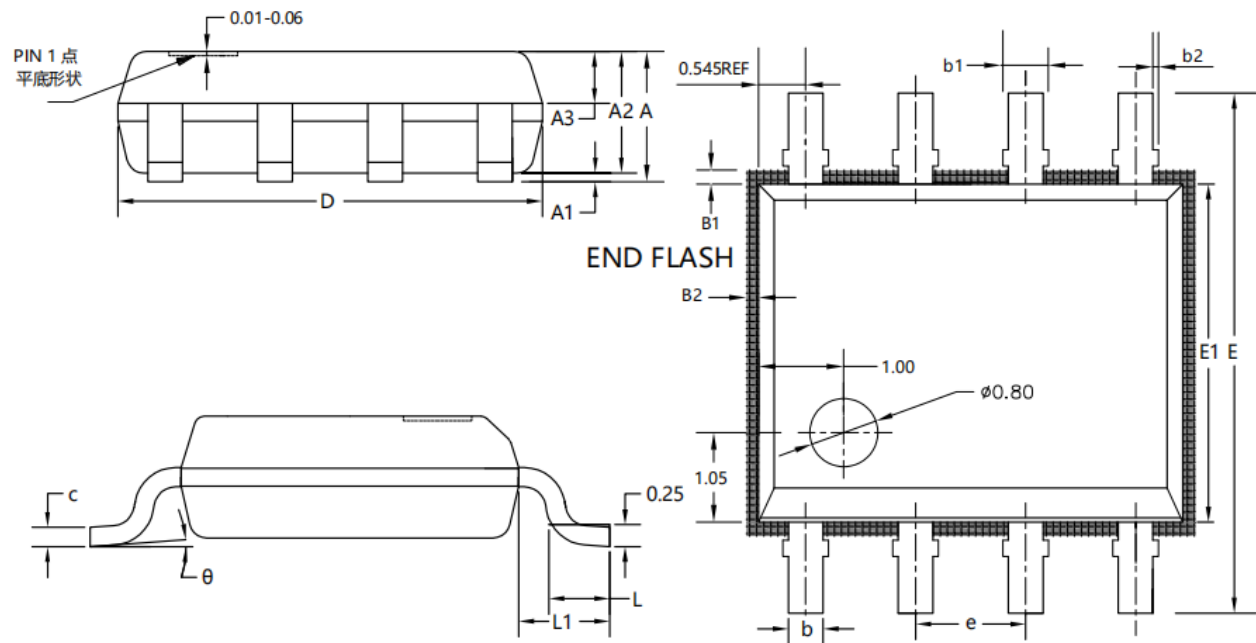
COMMON DIMENSIONS: UNITS OF MEASURE=MILLIMETER

Symbol	Dimensions		Symbol	Dimensions	
	Min.	Max.		Min.	Max.
A	1.75		FL	0.50	0.80
A1	0.05	0.15	LP	1.25	1.30
A2	1.40	1.50	LL	1.1 BSC	
A3	0.623 BSC		LW	0.38	0.43
BL	4.92	5.08	TL	5.90	6.10
BW	3.70	4.10	Z	0.54	
FT	0.20	0.21	θ	0°	8°

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POD B(C)



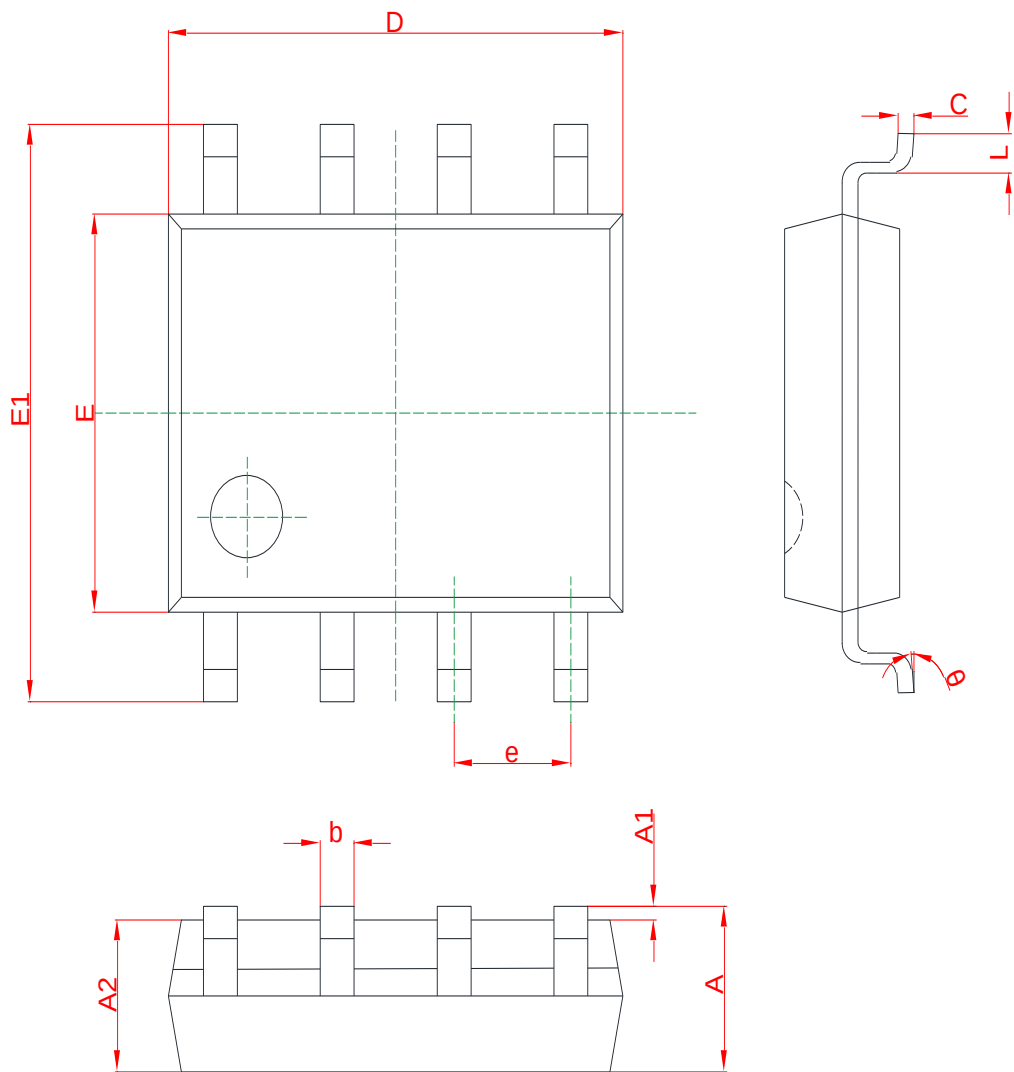
COMMON DIMENSIONS: UNITS OF MEASURE=MILLIMETER

Symbol	Dimensions			Symbol	Dimensions		
	Min.	NOM.	Max.		Min.	NOM.	Max.
A	1.55	1.65	1.75	L	0.50	0.60	0.70
A1	0.06	0.11	0.16	L1	0.90	1.05	1.20
A2	1.35	1.45	1.55	θ	0°	4°	8°
A3	0.60	0.70	0.80	B1	0.14MAX		
b	0.30	0.40	0.50	B2	0.12MAX		
c	0.17	0.20	0.25	b1	0.66MAX		
D	4.80	4.90	5.00	b2	0	0.04	0.08
E	5.80	6.00	6.20	e	1.27BSC		
E1	3.80	3.90	4.00				

ESP10N10C

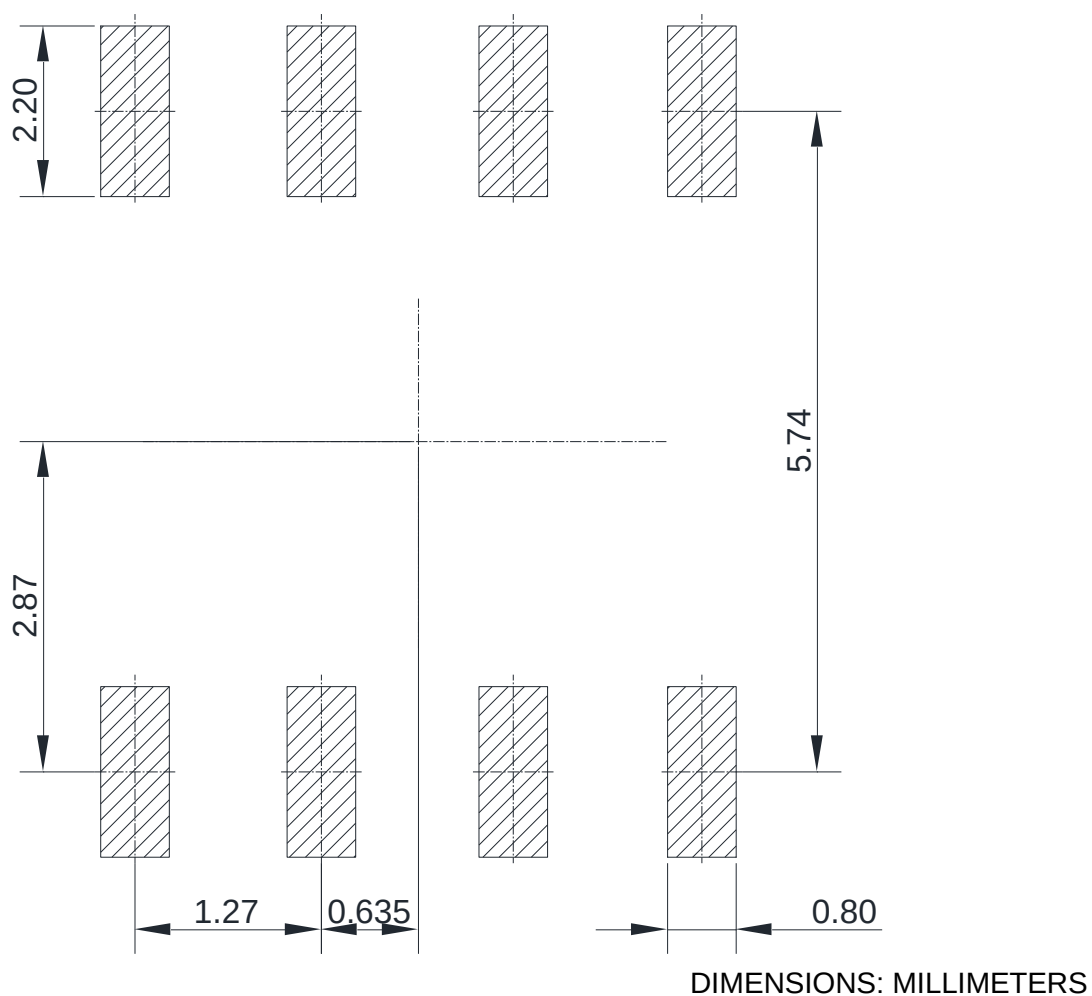
Rev-1.5

POD C(X)



Symbol	Dimensions		Symbol	Dimensions	
	Min.	Max.		Min.	Max.
L	0.40	0.60	e	1.27 TYP	
D	4.95	5.05	c	0.15	0.25
E	3.8	4.0	A2	1.33	1.50
E1	5.80	6.20	A1	0.04	0.20
b	0.4 TYP		θ	0°	8°

9. Recommended Soldering Footprint



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